

Darlington Complementary Silicon Power Transistors

...designed for general purpose and low speed switching applications.

- High DC Current Gain —
 $h_{FE} = 2500$ (typ.) at $I_C = 4.0$
- Collector-Emitter Sustaining Voltage at 100 mAdc
 $V_{CEO(sus)} = 80$ Vdc (min.) — BDX33B, 34B
 100 Vdc (min.) — BDX33C, 34C
- Low Collector-Emitter Saturation Voltage
 $V_{CE(sat)} = 2.5$ Vdc (max.) at $I_C = 3.0$ Adc — BDX33B, 33C/34B, 34C
- Monolithic Construction with Build-In Base-Emitter Shunt resistors
- TO-220AB Compact Package

MAXIMUM RATINGS

Rating	Symbol	BDX33B BDX34B	BDX33C BDX34C	Unit
Collector-Emitter Voltage	V_{CEO}	80	100	Vdc
Collector-Base Voltage	V_{CB}	80	100	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous Peak	I_C	10 15		Adc
Base Current	I_B	0.25		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	70 0.56		Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150		$^\circ\text{C}$

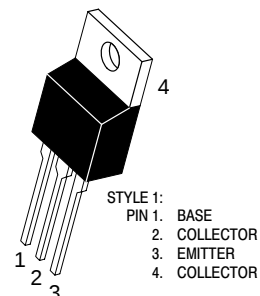
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.78	$^\circ\text{C/W}$

NPN
BDX33B
BDX33C*
PNP
BDX34B
BDX34C*

*ON Semiconductor Preferred Device

DARLINGTON
10 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
80-100 VOLTS
70 WATTS



CASE 221A-09
TO-220AB

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

BDX33B BDX33C BDX34B BDX34C

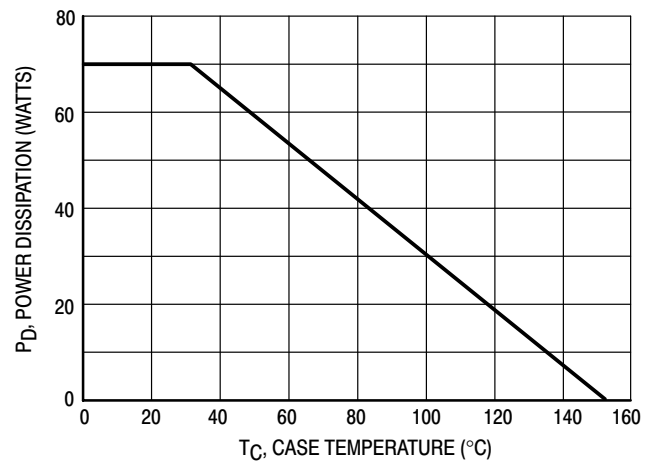


Figure 1. Power Derating

BDX33B BDX33C BDX34B BDX34C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage ¹ ($I_C = 100\text{ mAdc}$, $I_B = 0$)	BDX33B/BDX34B BDX33C/BDX34C	$V_{CEO(sus)}$	80 100	— —	Vdc
Collector–Emitter Sustaining Voltage ¹ ($I_C = 100\text{ mAdc}$, $I_B = 0$, $R_{BE} = 100$)	BDX33B/BDX34B BDX33C/BDX33C	$V_{CER(sus)}$	80 100	— —	Vdc
Collector–Emitter Sustaining Voltage ¹ ($I_C = 100\text{ mAdc}$, $I_B = 0$, $V_{BE} = 1.5\text{ Vdc}$)	BDX33B/BDX34B BDX33C/BDX34C	$V_{CEX(sus)}$	80 100	— —	Vdc
Collector Cutoff Current ($V_{CE} = 1/2$ rated V_{CEO} , $I_B = 0$)	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_{CEO}	— —	0.5 10	mAdc
Collector Cutoff Current ($V_{CB} = \text{rated } V_{CBO}$, $I_E = 0$)	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_{CBO}	— —	1.0 5.0	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)		I_{EBO}	—	10	mAdc

ON CHARACTERISTICS

DC Current Gain ¹ ($I_C = 3.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	BDX33B, 33C/34B, 34C	h_{FE}	750	—	—
Collector–Emitter Saturation Voltage ($I_C = 3.0\text{ Adc}$, $I_B = 6.0\text{ mAdc}$)	BDX33B, 33C/34B, 34C	$V_{CE(sat)}$	—	2.5	Vdc
Base–Emitter On Voltage ($I_C = 3.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	BDX33B, 33C/34B, 34C	$V_{BE(on)}$	—	2.5	Vdc
Diode Forward Voltage ($I_C = 8.0\text{ Adc}$)		V_F	—	4.0	Vdc

¹ Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

² Pulse Test non repetitive: Pulse Width = 0.25 s.

BDX33B BDX33C BDX34B BDX34C

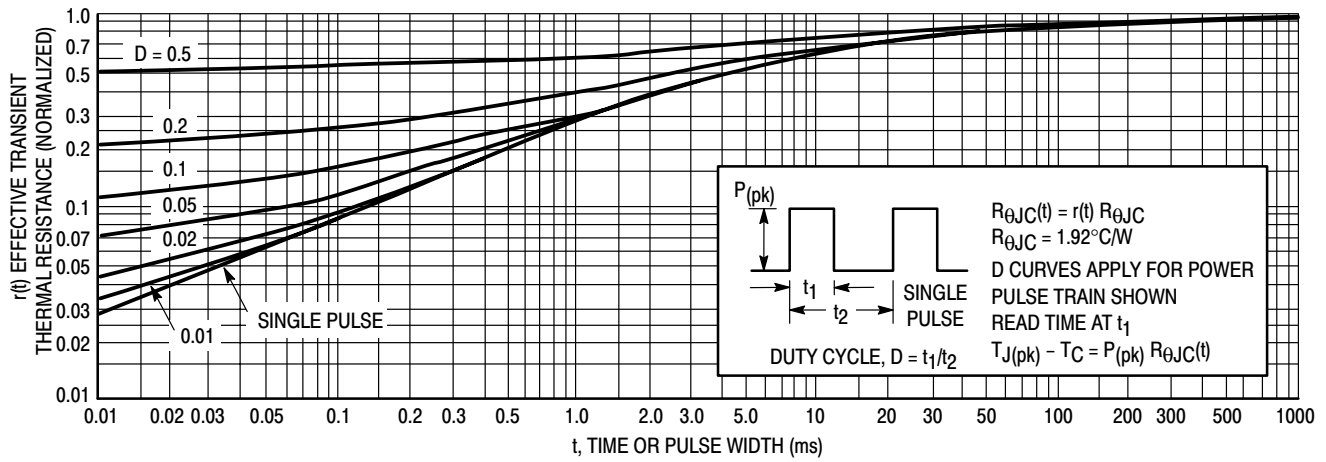


Figure 1. Thermal Response

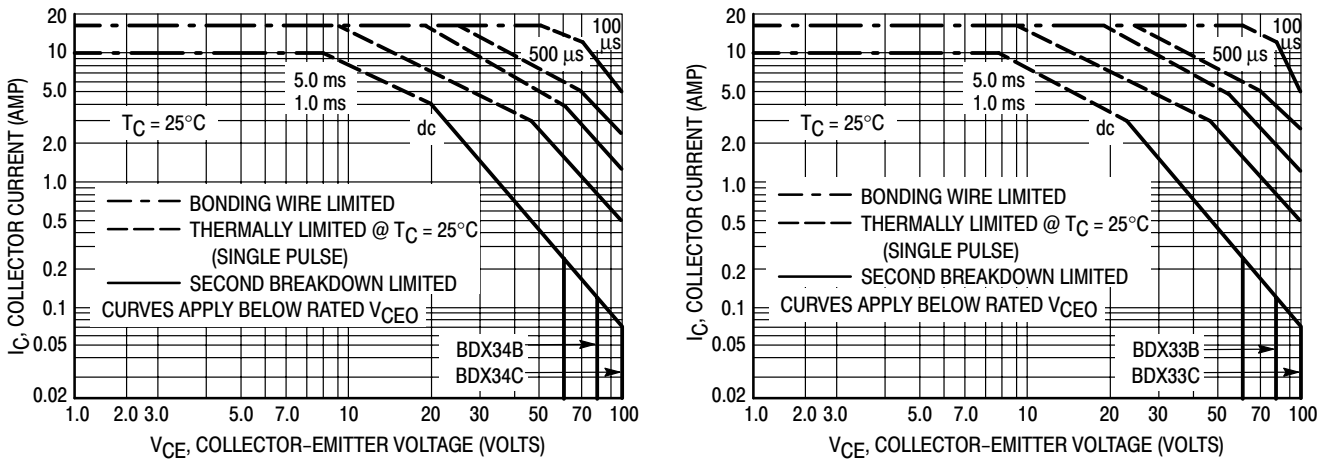


Figure 2. Active-Region Safe Operating Area

BDX33B BDX33C BDX34B BDX34C

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 3 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on

conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} = 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

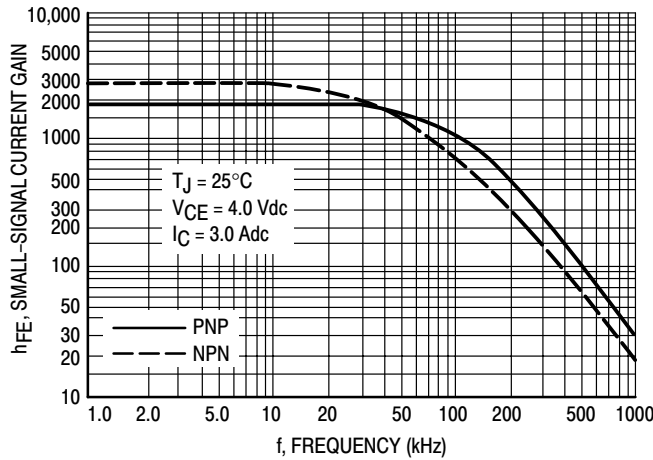


Figure 3. Small-Signal Current Gain

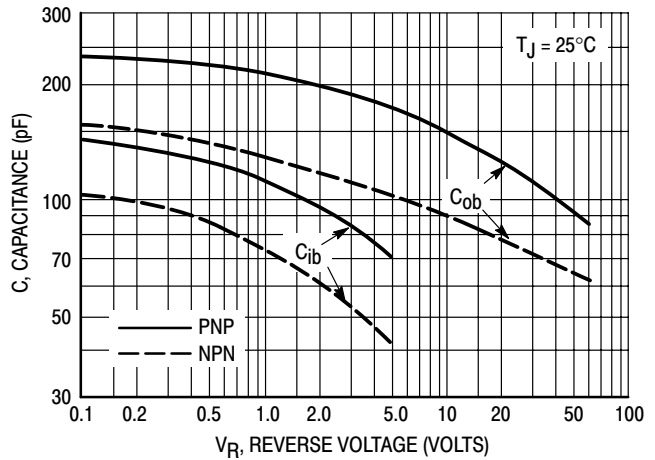
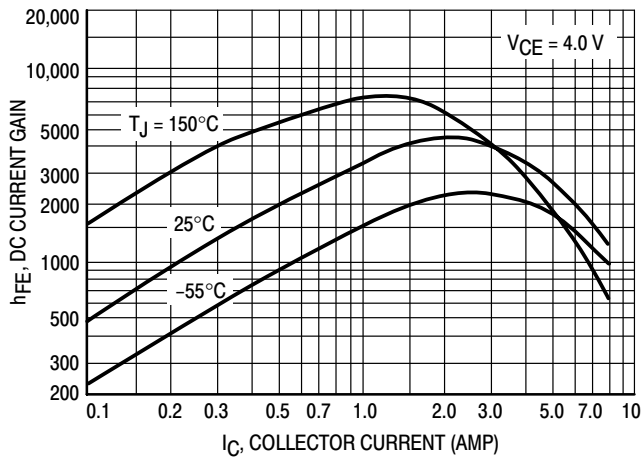


Figure 4. Capacitance

BDX33B BDX33C BDX34B BDX34C

NPN
BDX33B, 33C



PNP
BDX34B, 34C

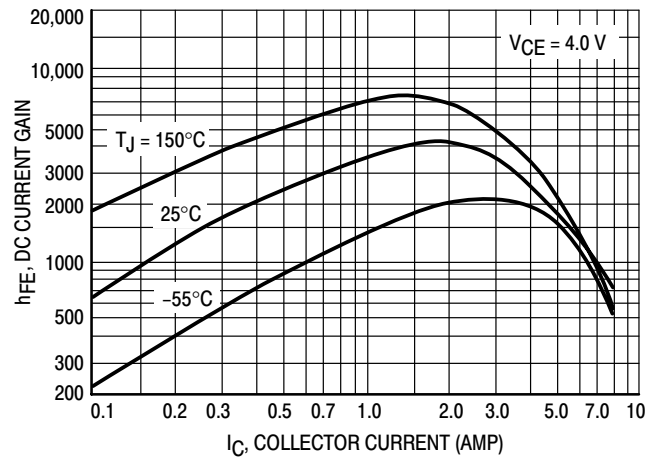


Figure 5. DC Current Gain

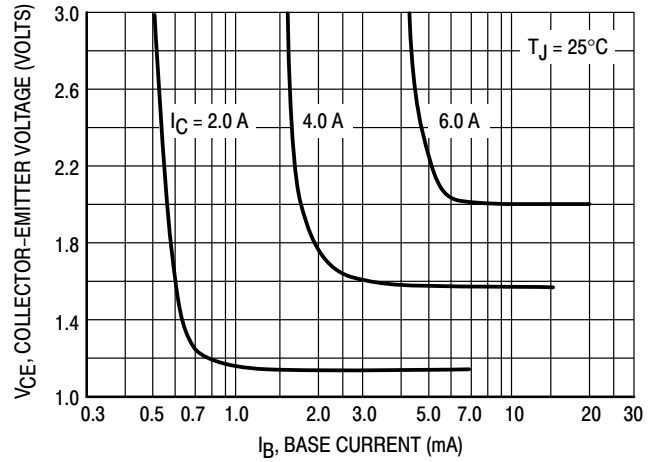
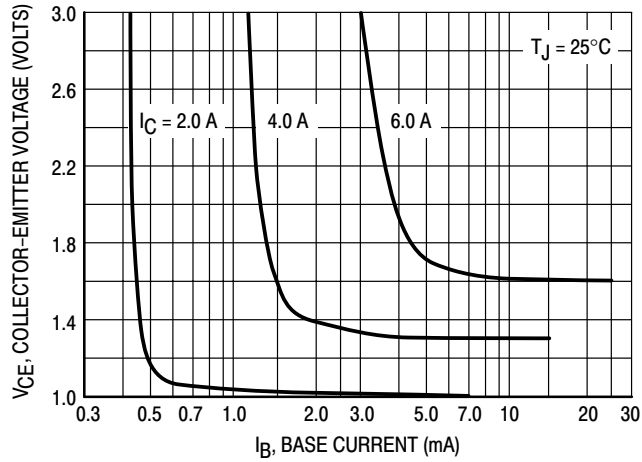


Figure 6. Collector Saturation Region

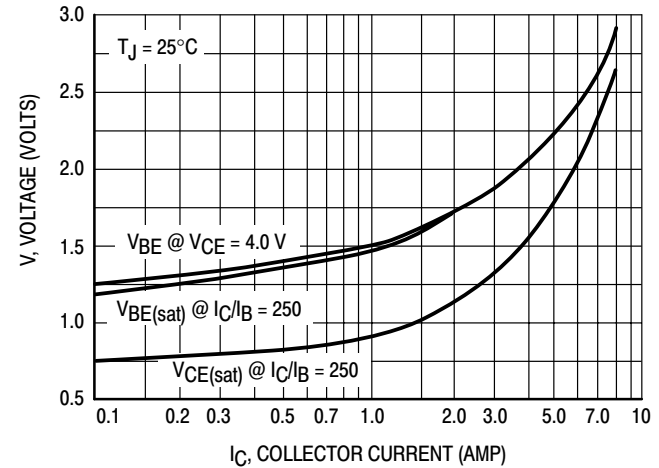
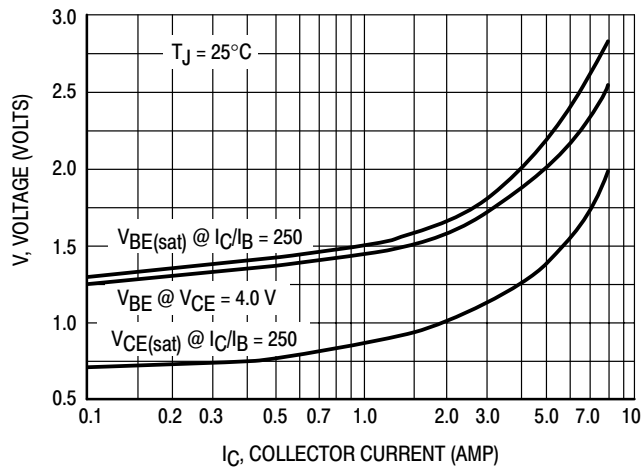
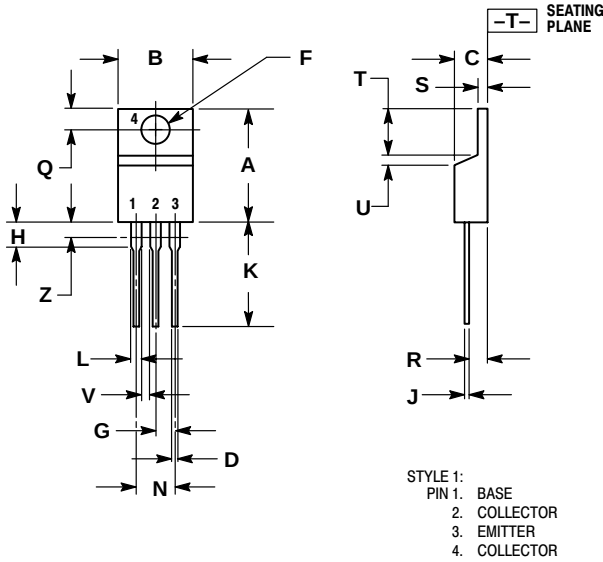


Figure 7. "On" Voltages

BDX33B BDX33C BDX34B BDX34C

PACKAGE DIMENSIONS

TO-220AB
CASE 221A-09
ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

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